IHSM12R021F1

V_{DSS}	1200 V
$R_{DS(on)}$	21 mΩ

HAWKPACK PF1 series

1200 V, 21 mΩ, Silicon Carbide, Full-bridge Module



Press-fit low-profile

Features

- Complete H-bridge in one module
- Baseplate-less, press-fit pins
- Short commutation loops for fast switching

Typical applications

- Isolated DC-DC converters (dual active bridge, phase-shifted full bridge)
- EV chargers
- Battery energy storage

Description

1200 V, 21 mΩ silicon-carbide MOSFET full-bridge module in a 62.8 × 33.8 mm baseplate-less housing.

Key specifications

Parameter	Value
V_{DSS}	1200 V
$R_{DS(on)}$ typ., T_{vj} = 25 °C	21 mΩ
I_D nominal	48 A
Topology	Full-bridge
T_{vj} op. max	175 °C
Outline	62.8 × 33.8 mm, baseplate-less, press-fit pins

Full characterization data

Thermal resistance, switching energies and times, capacitances, gate charge and typical characteristic curves for IHSM12R021F1 are available on request: request the full data or write to sales@ironhawksemi.com.

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Package

Press-fit low-profile. Mechanical outline drawing, STEP model and PCB footprint available on request.

Ordering information

Part number	Packing	MOQ	Lead time
IHSM12R021F1	Box	On request	On request

Information in this document is believed to be accurate but is subject to change without notice. Typical values are not guaranteed. The customer is responsible for validating suitability in the end application. IRONHAWK · sales@ironhawksemi.com

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